

# TECHNICAL DATA

## VT01

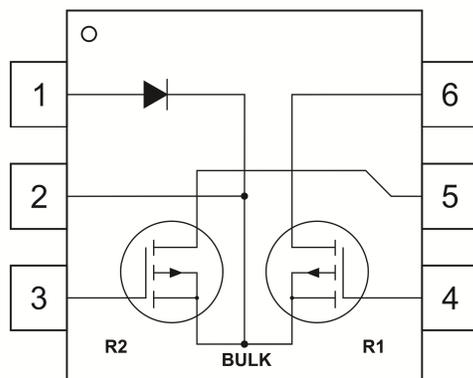
### 400nm RADFET

### in 6L SOT-23 Plastic package

## VT01 Description and Pin-Out

The VT01 is Varadis 400nm RADFET chip packaged in a plastic SOT-23 six lead package.

The part consists of two identical RADFETs, R1 and R2, and a diode (see Figure 1 and Table 1). The RADFETs' gate oxide thickness is 400nm and W/L is 300 $\mu$ m/50 $\mu$ m. The RADFETs have individual gate and drain terminals, while the source and bulk are common and connected together; this is also the diode bulk contact.



**Figure 1:** VT01 pin-out drawing.

**Table 1:** VT01 pin-out description.

Pin Number	Description
1	Diode anode
2	Source/bulk (common)
3	Gate of R2
4	Gate of R1
5	Drain of R2
6	Drain of R1

## Maximum Ratings

Maximum ratings of the VT01 RADFET are given in Table 2.

**Table 2:** Maximum ratings of the VT01. Measured at room temperature.

Characteristics	Symbol	Specification	Unit	Remarks
Drain-Source Voltage	$V_{DS}$	-25	V	
Gate-Source Voltage	$V_{GS}$	+/- 50	V	
Drain-Gate Voltage	$V_{DG}$	-50	V	
Drain Current	$I_D$	-1	mA	Continuous
Source Current	$I_S$	-1	mA	Continuous
Soldering Temperature	$T_{sol}$	+250	$^{\circ}$ C	

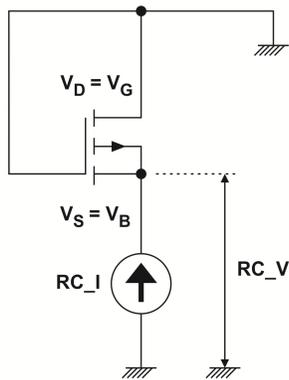
## Modes of Operation

### Irradiation Mode (Sense Mode)

In this mode of operation it is recommended that all terminals of the RADFET are connected to ground. For alternative biasing options, contact the manufacturer.

### Read-Out Mode (Accumulated Radiation Dose Read-Out)

The RADFET can be read at arbitrary intervals, depending on the application. The period between readings can be from seconds to days or even months. The circuit used to read out the RADFET (Reader Circuit - RC) is shown in Figure 2 with connection configuration in Table 3.

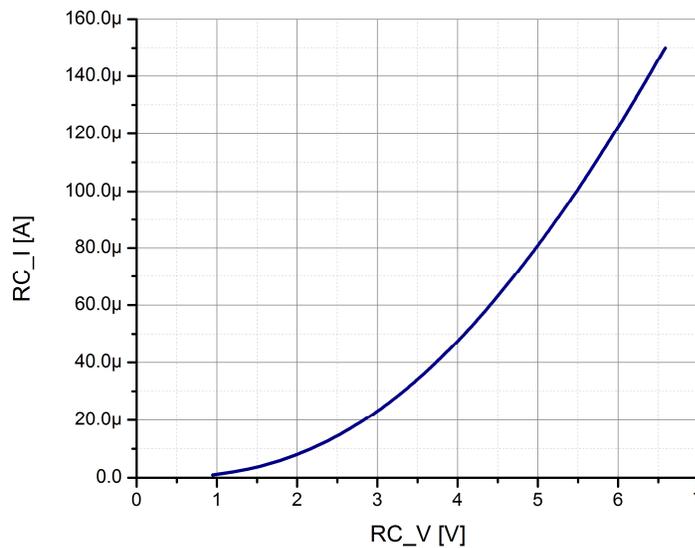


**Table 3:** Connections in Read-Out mode.

Terminal	Bias
S=B	Current is forced (RC_I) Voltage reading is taken (RC_V)
G=D	0V (common)

**Figure 2:** Reader Circuit (RC) configuration.

Current  $RC\_I$  is forced into the RADFET, connected in RC configuration (Figure 2). The voltage at the source ( $RC\_V$ ) is measured; this voltage is called “RC threshold voltage”. Typical I-V curve for the un-irradiated device in this configuration is shown in Figure 3. In principle, any read-out current ( $RC\_I$ ) value above  $5\mu\text{A}$  can be chosen, as long as the value is kept unchanged after the start of radiation exposure. For best temperature compensation, the  $RC\_I$  value of  $10\mu\text{A}$  is recommended.



**Figure 3:** Typical Reader Circuit (RC) I-V curve, pre-irradiation. Measured at room temperature.

## Electrical Parameters

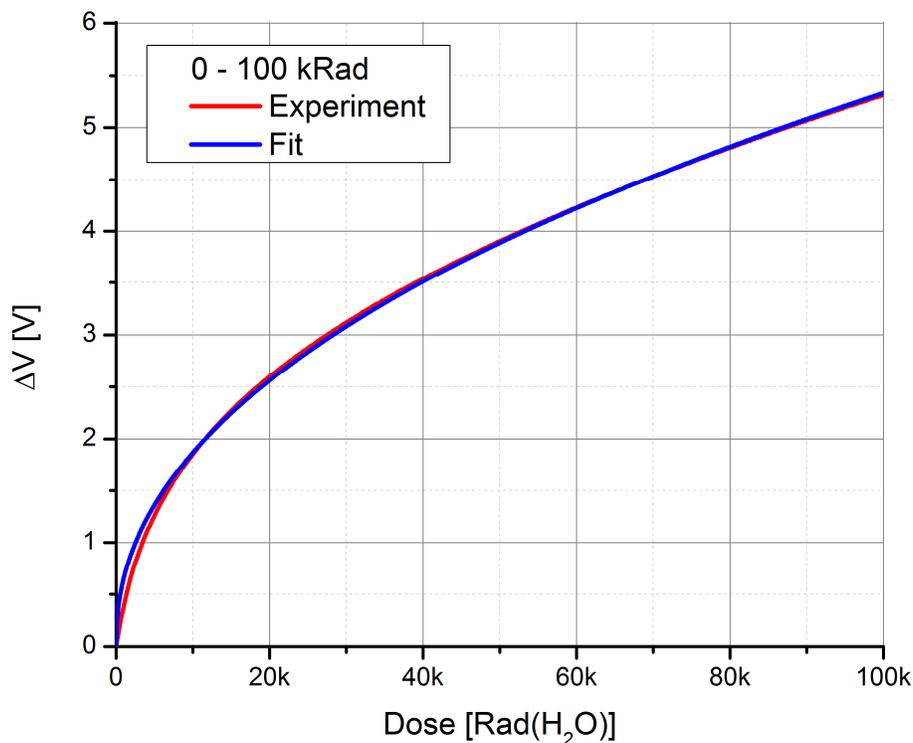
The most important electrical parameter of un-irradiated RADFET is RC threshold voltage (RC\_V). Specification for RC\_V is given in Table 4. Results of RC\_V measurements prior to shipment are included in documentation that comes with ordered parts. Typically, the range of RC\_V of delivered parts is significantly tighter than in the specification.

**Table 4:** Specification for RC threshold voltage. Measured at room temperature.

Parameter	Symbol	Test Circuit and Conditions	Limits		Unit
			Min	Max	
RC Threshold Voltage	RC_V	Figure 2 and Table 3 RC_I = 10 $\mu$ A	0.8	3.0	V

## Calibration Data

The calibration curve for the RADFET shows evolution of  $\Delta V$  (the change in RC threshold voltage with reference to its pre-irradiation value) with dose. Note that a specific calibration curve, obtained using the Co-60 source, is associated with each RADFET production batch. The calibration curve, together with analytical equation and fitting coefficients, will be provided with the supplied parts. For illustration, typical calibration curve is shown in Figure 4.



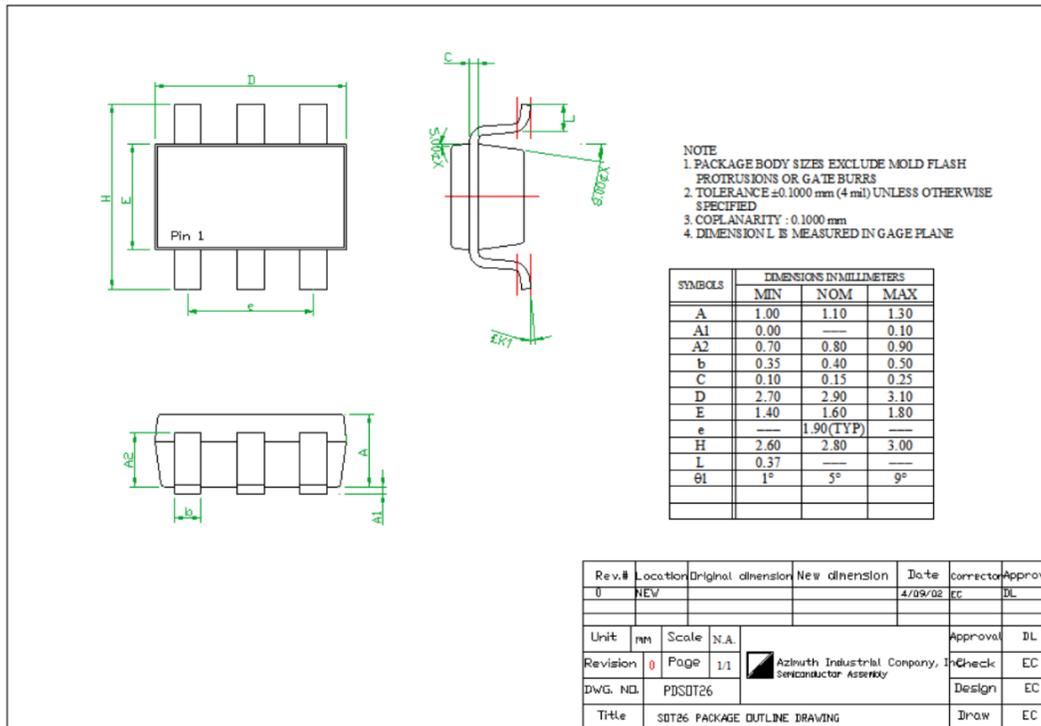
**Figure 4:** Typical calibration curve indicating change in RC\_V during irradiation. Irradiation at room temperature with Co-60 gamma source, dose rate ~50 Gy/h (5 krad/h). All RADFET terminals grounded during irradiation. Measurements at room temperature.

## Package Information

VT01 package specifications are given in Table 5, and package diagram in Figure 5.

**Table 5:** VT01 package specifications.

Description	Specification
Package Type	Six-pin plastic SOT-23 package
Package Dimensions (L x W x H)	2.90 mm x 2.80 mm x 1.10 mm (see Figure 5)



**Figure 5:** VT01 package diagram.

## Notes

We calibrate our standard products at room temperature using a Co-60 gamma-ray source. Irradiation is performed in a single event at the dose rate of ~50 Gy[Si]/hour (5 krad[Si]/hour) and includes the dose range from 1–1,000 Gy (100 rad – 100 krad).

Customers whose requirements include conditions significantly different from the above should contact [support@varadis.com](mailto:support@varadis.com) to discuss the optimum way to implement the RADFETs for their specific applications.

The VT01 has a large dynamic range, from 1 cGy (1 rad) to 1 kGy (100 krad).

While the supplied calibration curve covers doses from 1–1,000 Gy, other measurements at room temperature show that lower doses, down to 1cGy, can be detected. The lower the minimum dose required by the customer, the more accurate must be the RADFET temperature compensation and read-out electronics. Please contact [support@varadis.com](mailto:support@varadis.com) for further details if your application includes lower dose range.

Regarding the high end of the dose range, VT01 can measure doses even higher than 1 kGy (100 krad). However, the sensitivity decreases with dose and it depends on the actual application requirements whether this sensitivity loss is acceptable. As VT01 comes calibrated up to 1 kGy (100 krad), additional calibration is needed for measurements beyond this limit.